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INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)	Applicant: Kie Y. Ahn et al.	
	Filing Date: Herewith	Group: Unknown 2818 S-4324 09/09/97 08/30/01

U. S. PATENT DOCUMENTS

**Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
PP	5,668,035	09/16/1997	Fang, C.H., et al.	438	239	06/10/96
↑	5,985,725	11/16/1999	Chou, J.	438	294	12/23/97
↓	6,087,225	07/11/2000	Bronner, G.B., et al.	438	275	02/05/98
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FOREIGN PATENT DOCUMENTS

**Examiner Initial	Document Number	Date	Country	Class	Subclass	Translation Yes No

OTHER DOCUMENTS

(Include Article, Title, Date, Institution, Etc.)

PP	Chen, Y., et al., "Performance and Reliability Assessment of Dual-Gate CMOS Devices with Gate Oxide Grown Nitrogen Implanted Si Substrates", <u>International Electron Device Meeting</u> , pg. I-4, (1997)
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PP	Fujiwara, M., et al., "New Optimization Guidelines for Sub-0.1 micrometer CMOS Technologies with 2 micrometer NO Gate Oxynitrides", <u>1999 Symposium on VLSI Technology Digest of Technical Papers</u> , pp. 121-122, (1999)
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Date Transcribed

4/3/2002

The undersigned certifies that he or she is the patent attorney or agent of record in the above identified application.

**I hereby declare that all statements made herein are true and complete to the best of my knowledge.

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